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(54) **LIQUID CRYSTAL DISPLAY DEVICE**

(57) **ABSTRACT**

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In a liquid crystal display device having a reflection electrode of a reflection diffuser panel shape formed with surface roughness, a liquid crystal orientation film for realizing a predetermined pre-tilt angle is formed on the reflection electrode by an optical orientation technique. A liquid crystal display device having a reflection electrode of a reflection diffuser panel shape formed with surface roughness provided on a driving substrate and an ultraviolet-reactive liquid crystal orientation film formed on the reflection electrode, is produced by step (1) for forming a protective film made of a material transparent to a visible light for absorbing an ultraviolet light on the reflection electrode on the driving substrate side so as to eliminate the level difference in the surface roughness of the reflection electrode; step (2) for coating a composition for an ultraviolet-reactive liquid crystal orientation film onto the protective film; and step (3) for forming a liquid crystal orientation film on the coating film of the composition for a liquid crystal orientation film by irradiating a polarizing ultraviolet light L onto the substrate surface in the slanting direction.

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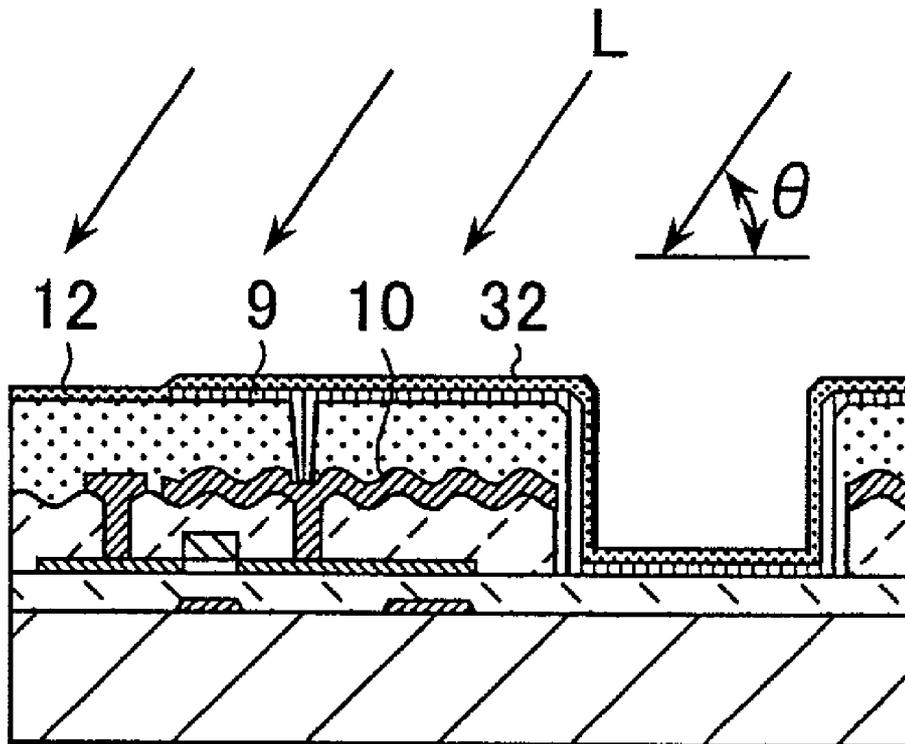


FIG.1A

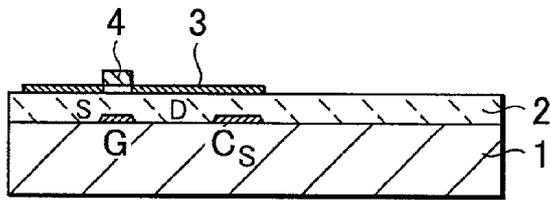


FIG.1B

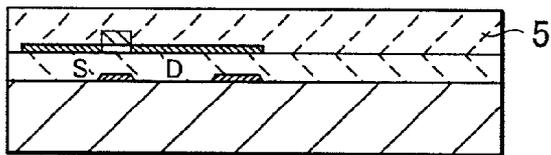


FIG.1C

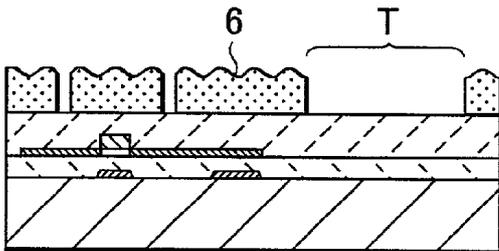


FIG.1D

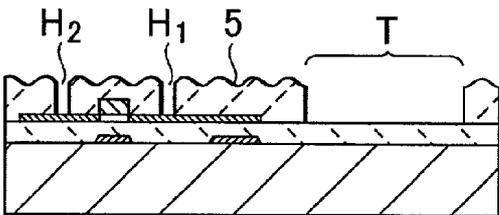


FIG.1E

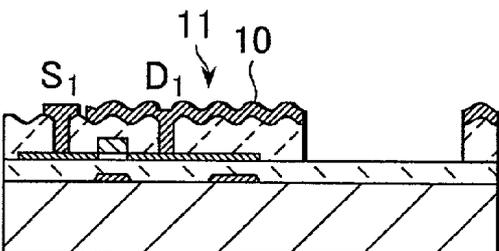


FIG.1F

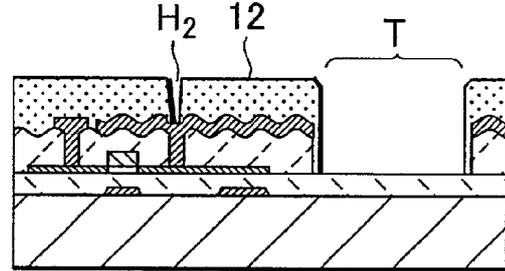


FIG.1G

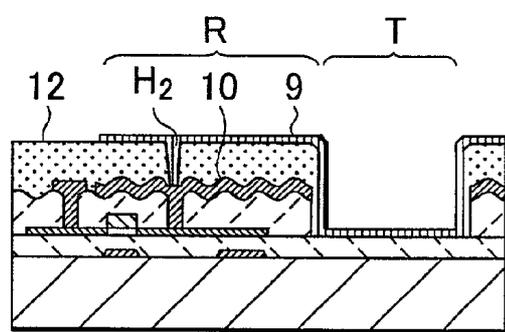


FIG.1H

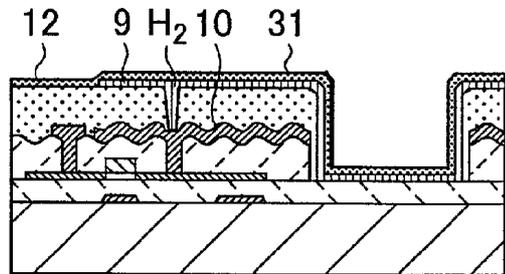


FIG.1I

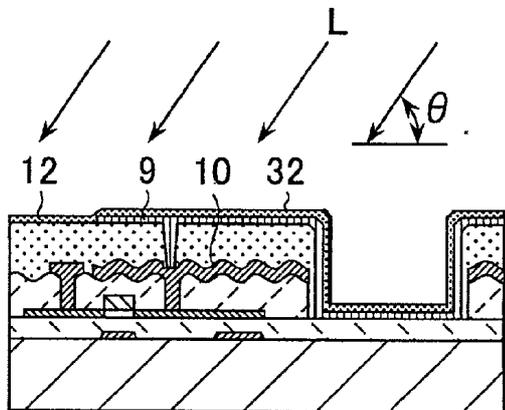


FIG.2A

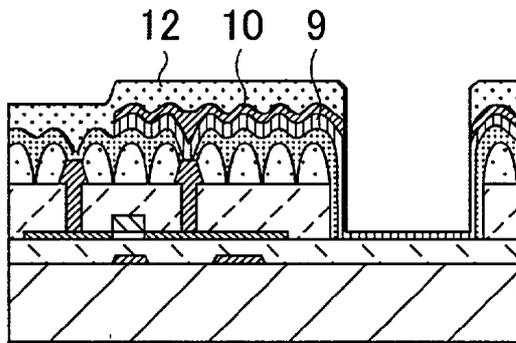


FIG.2B

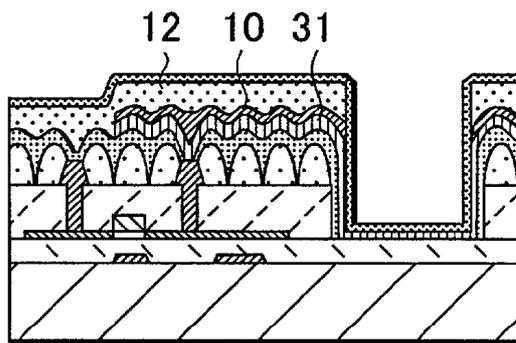


FIG.2C

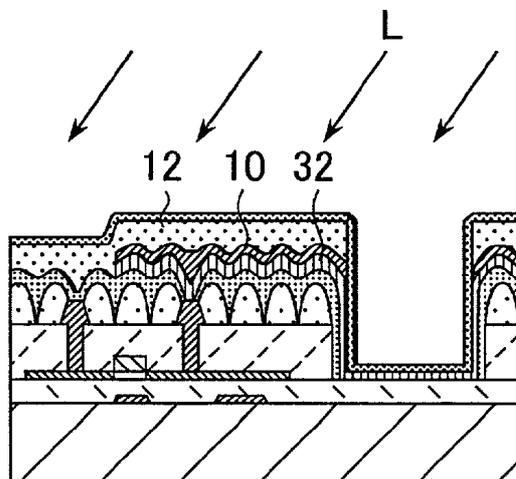


FIG.3

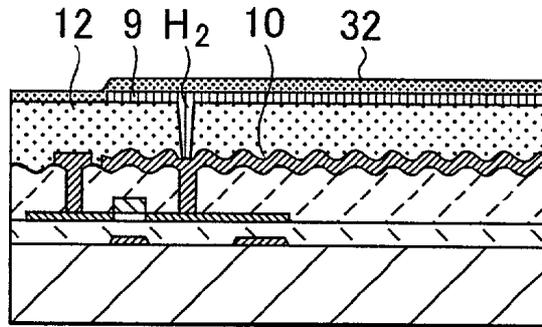


FIG.4

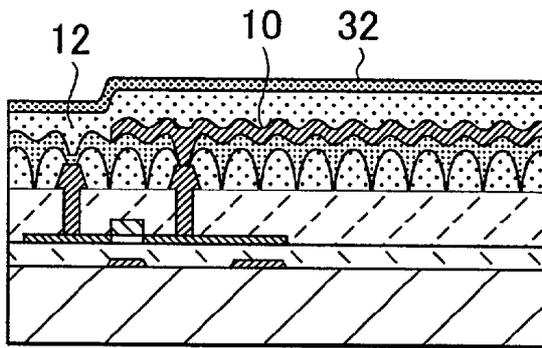


FIG.5

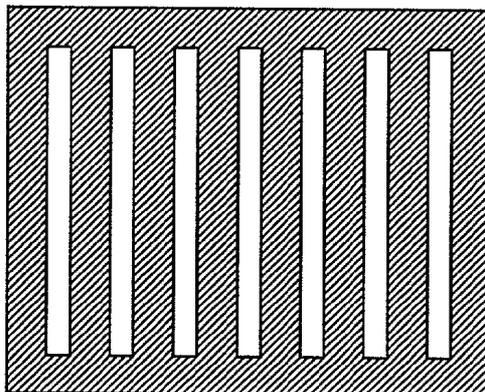


FIG.6

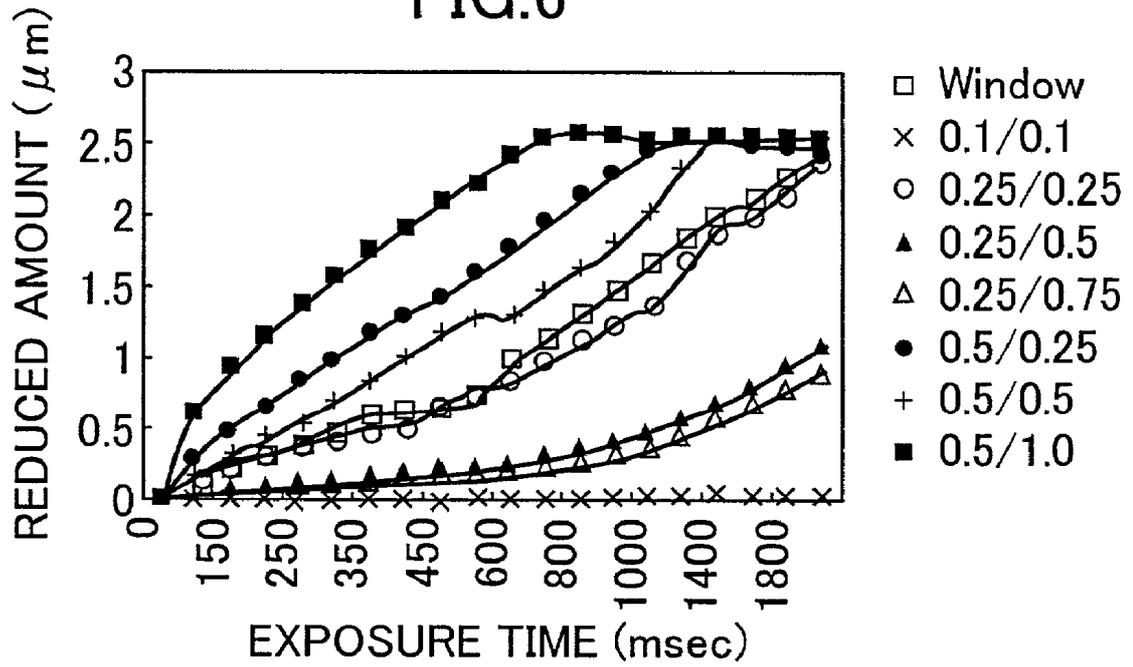


FIG.7

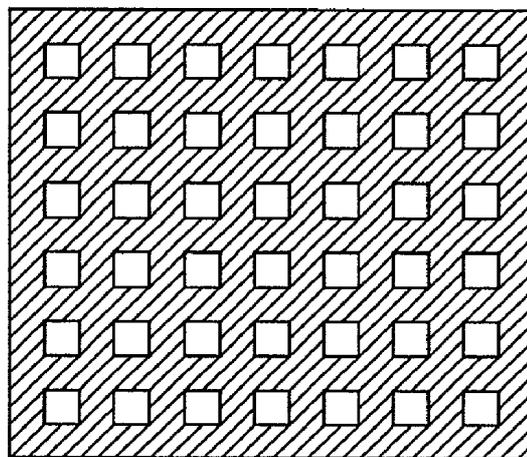


FIG.8

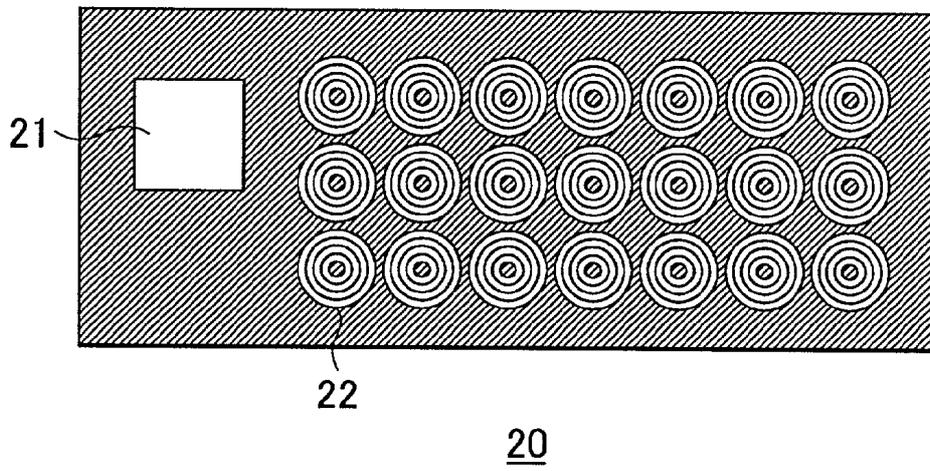


FIG.9A

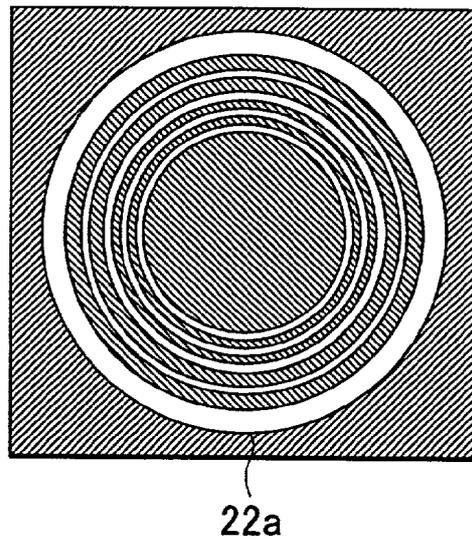


FIG.9B

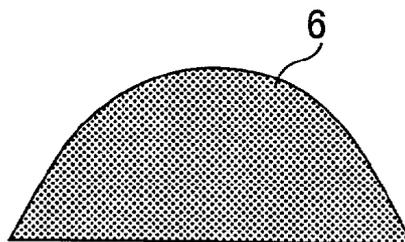


FIG.10A

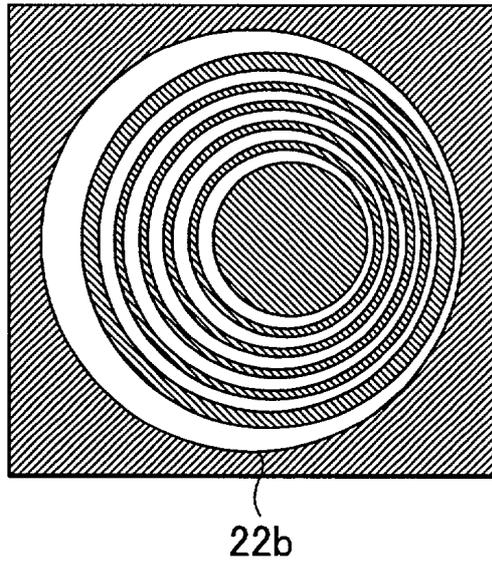


FIG.10B

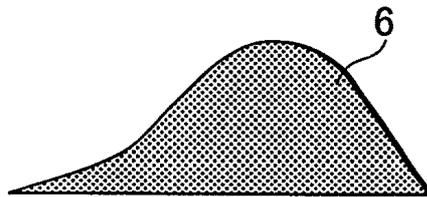


FIG.11

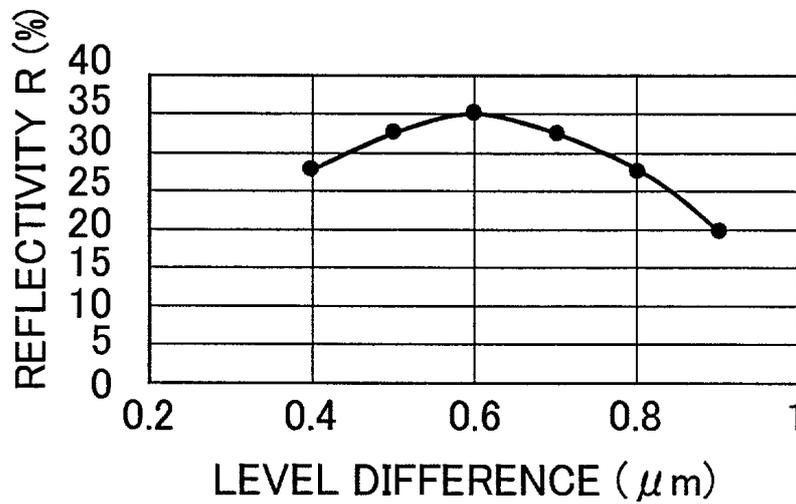


FIG. 12A

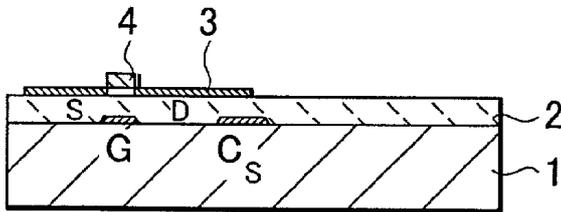


FIG. 12B

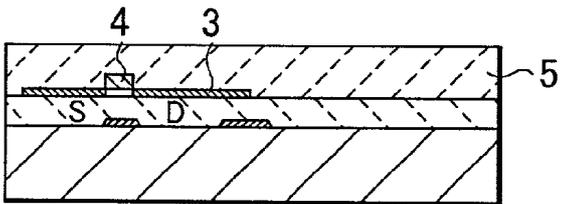


FIG. 12C

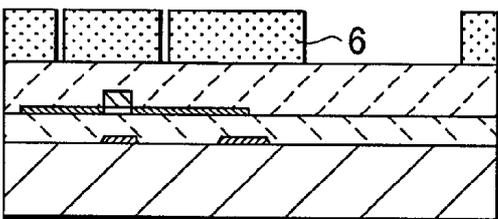


FIG. 12D

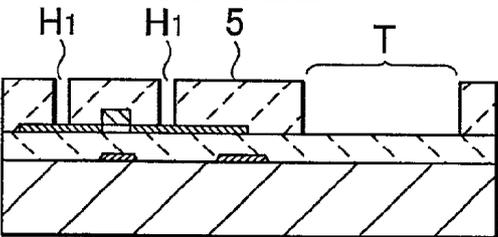


FIG. 12E

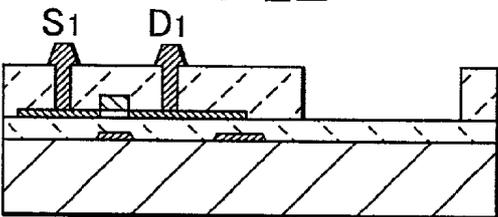


FIG. 12F

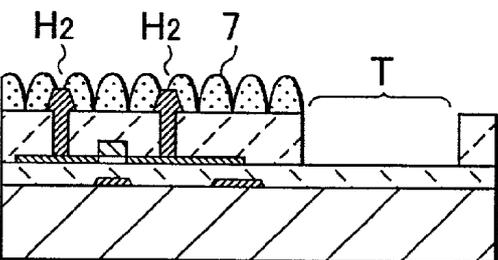


FIG. 12G

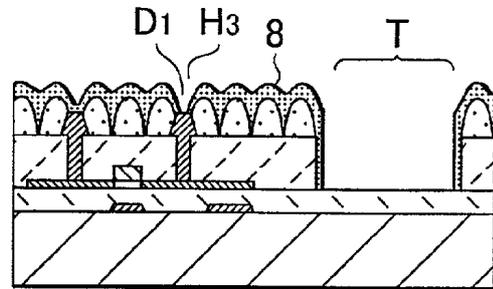


FIG. 12H

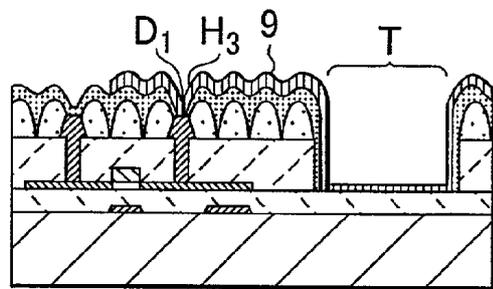


FIG. 12I

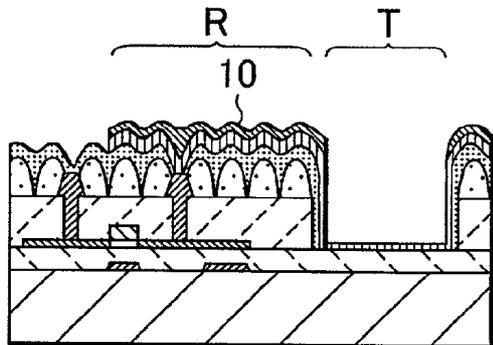


FIG. 12J

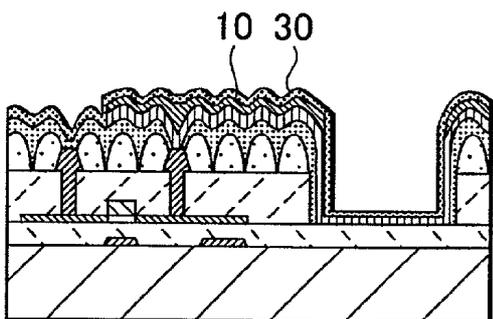


FIG.13

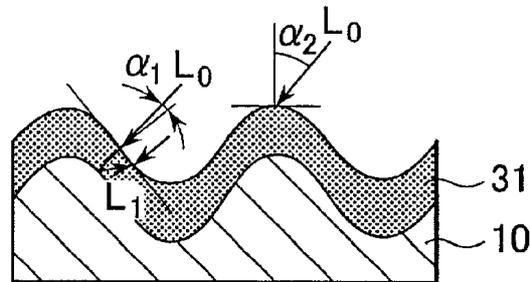
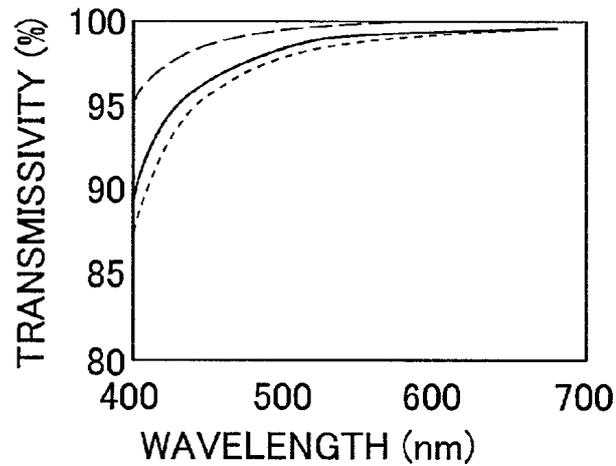


FIG.14



- (--- 405G MANUFACTURED BY JSR, FILM THICKNESS $1.3 \mu\text{m}$ (FIRST LAYER AND SECOND LAYER))
- (——— 415G MANUFACTURED BY JSR, FILM THICKNESS $2.6 \mu\text{m}$)
- (..... 415G MANUFACTURED BY JSR, FILM THICKNESS $3.2 \mu\text{m}$)

LIQUID CRYSTAL DISPLAY DEVICE

BACKGROUND OF THE INVENTION

[0001] 1. Field of the Invention

[0002] The present invention relates to a liquid crystal display device provided with a reflection electrode of a reflection diffuser panel shape formed with surface roughness and more specifically to a technique for forming an ultraviolet-reactive liquid crystal orientation film on the reflection electrode.

[0003] 2. Description of the Related Art

[0004] The driving side TFT substrate of an active matrix type liquid crystal display device has, in the reflection part of a pixel, a reflection electrode of a reflection diffuser panel shape formed with surface roughness and having, in the transmission part of the pixel, a transparent electrode consisting of a transparent conductive film, thereby performing semi-transmission liquid crystal display. The driving side TFT substrate has hitherto been produced as shown in FIGS. 12A to 12J. FIGS. 12A to 12J show the processes for producing a liquid crystal display device having a TFT of a bottom gate construction in a pixel structure. A liquid crystal display device having a TFT of a top gate construction in a pixel structure is basically produced by the same production process.

[0005] As shown in FIG. 12A, a metal film is deposited on a transparent substrate 1, and then, is dry etched using a photolithographic method to form a gate G and an auxiliary capacity electrode Cs. Thereafter, a gate insulating film 2 is laminated thereon to form a polysilicon film 3.

[0006] To prevent impurities doping to a channel part during impurities doping to a source region and a drain region, a stopper 4 is formed on the polysilicon film 3 as the channel part so as to be in a self-alignment manner to the gate G, thereby performing impurities doping to the source region and the drain region.

[0007] Thereafter, the polysilicon film 3 is separated in an island form using a photoresist process and an etching process to form a low-temperature polysilicon thin film transistor (TFT).

[0008] An interlayer insulating film 5 is formed (FIG. 12B) To form contact holes and an opening of the transmission part of a pixel, the photoresist layer 6 is formed on the interlayer insulating film 5. A mask with a pattern opening the contact hole forming parts the transmission part of the pixel as a photo mask is used to pattern the photoresist layer 6 by the photolithographic method (FIG. 12C). Using this as an etching mask, the interlayer insulating film 5 is etched to form contact holes H_1 and an opening of a transmission part T of the pixel in the interlayer insulating film 5 (FIG. 12D).

[0009] A metal film is deposited by sputtering, and then, is etched to form a source electrode S_1 and a signal wiring connected through the contact hole H_1 to the source S of a TFT and a drain electrode D_1 connected through the contact hole H_1 to the drain D of the TFT (FIG. 12E)

[0010] A rough shape as the underlayer of the surface roughness shape of a reflection electrode having reflection diffusion ability is formed as follows, using two layers made of a photoresist material. A first layer 7 forming a basic

rough construction is formed using a photoresist material by the photolithographic method (FIG. 12F). There is used a photo mask opening a second contact hole H_2 to be conductive with the source electrode S_1 or the drain electrode D_1 and the transmission part T of the pixel. A second layer 8 for improving the reflection properties is formed using a photoresist material similar to that of the first layer 7 by the photolithographic method (FIG. 12FG). There is used a mask, as in the first layer 7, opening a third contact hole H_3 to be conductive with the drain electrode D_1 and the transmission part T of the pixel. A surface roughness shape consisting of two layers of the first layer 7 and the second layer 8 is thus formed.

[0011] A transparent conductive film 9 forming a transparent electrode of the transmission part T of the pixel is deposited using a sputtering method. The transparent conductive film 9 connected to the drain electrode D_1 by the contact hole H_3 (FIG. 12H). As shown in FIG. 12H, the transparent conductive film 9 is formed in the reflection part of the pixel and may be used as the underlayer of the reflection electrode.

[0012] A metal film such as Al or Ag having a high reflectivity is deposited in a reflection part R of the pixel to form a reflection electrode 10 using the photolithographic method (FIG. 12I).

[0013] A liquid crystal orientation film 30 is coated onto the entire surface of the substrate to perform an orientation process by a mechanical rubbing method (FIG. 12J). A TFT substrate having the orientation film 30 is thus completed.

[0014] A liquid crystal orientation film is also coated onto an opposing substrate formed with a color filter and an opposing transparent electrode to perform the orientation process. Thereafter, in order that both substrates hold a suitable gap, a gap material is used to superpose both substrates together by a sealing material. Liquid crystals are then implanted in the resulting substrates for sealing to provide a liquid crystal display panel.

[0015] In the prior art method for producing the driving side TFT substrate of the active matrix type semi-transmission liquid crystal display device shown in FIGS. 12A to 12J, since the orientation process is performed by the mechanical rubbing method, dust is caused during rubbing. This results in contamination of the substrate and defects due to a short circuit of the pixel electrode and the opposing electrode. Static damage due to friction is also caused. The producing yield will be lowered.

[0016] To such problems, in place of the mechanical rubbing method, there is proposed an optical orientation technique in which an organic film for a liquid crystal orientation film is coated onto a substrate which is then irradiated with a polarizing ultraviolet light, so that a chemical change corresponding to the polarizing direction of the ultraviolet light is caused in the organic film to give the orientation properties and a pre-tilt angle to a liquid crystal.

[0017] As shown in FIG. 13, using the prior art optical orientation technique, a coating film 31 made of a composition for a liquid crystal orientation film is formed on the reflection electrode 10 of a reflection diffuser panel shape formed with surface roughness, and then, is radiated with a polarizing ultraviolet light L_0 . Incident angles α_1 and α_2 of the polarizing ultraviolet light L_0 to the coating film 31 are

not constant depending on a position on the surface roughness. A predetermined pre-tilt angle cannot be obtained. The polarizing ultraviolet light L_0 passing through the coating film **31** made of a composition for a liquid crystal polarization film is reflected by the reflection electrode **10**. A reflection light L_1 thereof is irradiated again onto the coating film **31** (a re-irradiation phenomenon). A predetermined orientation process cannot be performed. The display quality is lowered significantly.

[0018] The liquid crystal orientation film is formed on the reflection electrode of a reflection diffuser panel shape formed with surface roughness. Similar problems are caused not only in the semi-transmission liquid crystal display device having in one pixel a reflection part formed with a reflection electrode and a transmission part made of a transparent conductive film, but also in a reflection type liquid crystal display device having a pixel electrode consisting only of a reflection electrode. They are also caused not only in the active matrix type liquid crystal display device but also in a passive type liquid crystal display device.

SUMMARY OF THE INVENTION

[0019] Accordingly, an object of the present invention is to provide a liquid crystal display device having a reflection electrode of a reflection diffuser panel shape formed with surface roughness in which when a liquid crystal orientation film is formed on the reflection electrode by an optical orientation technique without being affected by the surface roughness of the reflection electrode and a re-irradiation phenomenon from the reflection electrode, so as to realize a predetermined pre-tilt angle in the liquid crystal, thereby forming an image excellent in the display quality.

[0020] The present inventors have found the following facts. In a liquid crystal display device having a reflection electrode of a reflection diffuser panel shape formed with surface roughness, a protective film for eliminating the level difference in the surface roughness of a reflection electrode is formed on the reflection electrode by a material transparent to a visible light for absorbing an ultraviolet light, a coating film made of a composition for an ultraviolet-reactive liquid crystal orientation film is formed on the protective film, and a coating film is irradiated with a polarizing ultraviolet light to form a liquid crystal orientation film. The coating film made of a composition for a liquid crystal orientation film is formed flatly on the protective film. The incident angles of the polarizing ultraviolet light incident upon the coating film made of a composition for a liquid crystal orientation film are constant in any position of the coating film. The light passing through the coating film is reflected by the reflection electrode and is again incident upon the coating film. The intensity of the light is lowered significantly by the protective film between the coating film and the reflection electrode. The influence of the reflection light from the reflection electrode onto the orientation process of the coating film can be reduced greatly. The liquid crystal orientation film is thus formed to produce a high-quality liquid crystal display device, though the liquid crystal orientation film is formed on the reflection electrode by the optical orientation technique.

[0021] The present invention provides a method for producing a liquid crystal display device having a reflection

electrode of a reflection diffuser panel shape formed with surface roughness provided on a driving substrate and an ultraviolet-reactive liquid crystal orientation film formed on the reflection electrode, comprising the following steps (1) to (3) of:

[0022] (1) forming a protective film made of a material transparent to a visible light for absorbing an ultraviolet light on the reflection electrode on the driving substrate side so as to eliminate the level difference in the surface roughness of the reflection electrode;

[0023] (2) coating a composition for an ultraviolet-reactive liquid crystal orientation film onto the protective film; and

[0024] (3) forming a liquid crystal orientation film on the coating film of the composition for a liquid crystal orientation film by irradiating a polarizing ultraviolet light onto the substrate surface in the slanting direction.

[0025] In addition, the present invention provides a liquid crystal display device having a reflection electrode of a reflection diffuser panel shape formed with surface roughness provided on a driving substrate and an ultraviolet-reactive liquid crystal orientation film formed on the reflection electrode, wherein a protective film made of a material transparent to a visible light for absorbing an ultraviolet light is formed so as to eliminate the level difference in the surface roughness of the reflection electrode, and an ultraviolet-reactive liquid crystal orientation film is formed on the protective film.

[0026] According to the present invention, the liquid crystal display device is provided with the ultraviolet-reactive liquid crystal orientation film. Unlike the case that the liquid crystal orientation film is provided by the mechanical rubbing method, there are eliminated contamination and defects due to dust and static damage due to friction so as to improve the yield.

[0027] The protective film flattens the surface roughness of the reflection electrode. The protective film prevents the re-irradiation phenomenon due to the reflection light from the reflection electrode. Though the liquid crystal orientation film is formed on the reflection electrode by the optical orientation technique, a predetermined pre-tilt angle can be realized in the liquid crystal to form an image excellent in the display quality.

BRIEF DESCRIPTION OF THE DRAWINGS

[0028] FIGS. 1A to 1J are process explanatory views of a method for producing a liquid crystal display device according to the present invention;

[0029] FIGS. 2A to 2C are process explanatory views of a method for producing a liquid crystal display device according to the present invention;

[0030] FIG. 3 is a cross-sectional view of a TFT substrate obtained from the producing method of the present invention;

[0031] FIG. 4 is a cross-sectional view of a TFT substrate obtained from the producing method of the present invention;

[0032] FIG. 5 is a plan view of a photo mask having an L/S pattern;

[0033] FIG. 6 is a diagram showing the relation between L/S of a photo mask, exposure time, and the reduced amount of the film thickness of a photoresist layer in a photolithographic process of the photoresist layer;

[0034] FIG. 7 is a plan view of a photo mask having a dot pattern;

[0035] FIG. 8 is a plan view of a photo mask for use in a photoresist layer;

[0036] FIG. 9A is a plan view of the pattern of a photo mask forming surface roughness in a photoresist layer;

[0037] FIG. 9B is a side view of surface roughness of a photoresist layer formed using the mask of FIG. 9A;

[0038] FIG. 10A is a plan view of the pattern of a photo mask forming surface roughness in a photoresist layer;

[0039] FIG. 10B is a side view of surface roughness of a photoresist layer formed using the mask of FIG. 10A;

[0040] FIG. 11 is a diagram showing the relation between the level difference and reflectivity of surface roughness of a reflection electrode;

[0041] FIGS. 12A to 12J are production process views of a prior art active matrix type semi-transmission liquid crystal display device;

[0042] FIG. 13 is an explanatory view of a prior art operation of a reflection electrode and a coating film of a composition for an ultraviolet-reactive liquid crystal orientation film provided thereon; and

[0043] FIG. 14 is transmissivity characteristic diagram of a photoresist material forming a protective film.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0044] The present invention will be described hereinbelow in detail with reference to the drawings. In the respective drawings, similar reference numerals denote the same or equivalent components.

[0045] FIGS. 1A to 1I are process explanatory views of one embodiment of the present invention for producing a semi-transmission liquid crystal display device having a pixel structure of a TFT of a bottom gate construction. The methods of FIGS. 1A to 1I are largely different from prior art methods shown in FIGS. 12A to 12J in that a specific protective film 12 is formed on a reflection electrode 10 and an ultraviolet-reactive liquid crystal orientation film 32 is formed thereon. Further, the reflection electrode 10 is formed by steps (A) to (E) described below in detail. An insulating layer under the reflection electrode 10 is formed of a single layer construction (an interlayer insulating film 5) from a three-layer lamination construction shown in FIG. 12 (the interlayer insulating film 5 and the first layer 7 and the second layer 8 made of a photoresist material). The reflection electrode 10, a source electrode S_1 , and a drain electrode D_1 are formed at the same time. The production process of the TFT substrate is simplified significantly to improve the productivity.

[0046] In this method, as shown in FIG. 1A, a single layer film or a lamination film such as Mo, Cr, Al, Ta and W is first deposited on a transparent substrate 1, and is then dry etched using a photolithographic method to form a gate G and an auxiliary capacity electrode Cs. A silicon nitride film, a silicon oxide film, or a lamination film of these is formed as a gate insulating film by a sputtering method or a CVD method. A polysilicon film 3 is formed thereon. In a method for forming the polysilicon film 3, for example, a semiconductor layer is formed on the gate insulating film 2, a dehydrogenation process at high temperature is performed in order to lower the hydrogen concentration of the semiconductor layer, and crystallization is performed by excimer laser to convert the semiconductor layer to a polysilicon film. When the hydrogen concentration is below 1 atom %, the dehydrogenation process may be omitted. To stabilize the film quality, the gate insulating film and the semiconductor layer are preferably deposited continuously.

[0047] To prevent doping to a channel part during the impurities doping to the source region and the drain region, a stopper 4 is formed on the polysilicon film 3 as the channel part so as to be in a self-alignment manner to the gate G. The stopper 4 is formed as follows. A stopper film made of silicon oxide is deposited on the gate insulating film 2. A resist is coated thereon. The back surface of the resist layer is exposed using the gate G as a mask. The resist is patterned in the channel forming portion so as to be in a self-alignment manner to the gate G. The stopper film is etched using the resist as a mask. The stopper film is left in the channel forming portion.

[0048] Thereafter, impurities are doped in the source region and the drain region using an ion implantation method or an ion doping method to form a source S and a drain D. The polysilicon film is separated in an island form using a photoresist process and an etching process to form a TFT. The above-mentioned TFT forming method is a method for forming a low-temperature polysilicon thin film transistor. The producing method of the present invention can be applied likewise when an amorphous silicon thin film transistor is formed.

[0049] As a process for forming the reflection electrode 10, the following steps (A) to (E) are performed.

[0050] Step (A) An interlayer insulating film 5 made of an inorganic insulating substance such as a silicon nitride film, a silicon oxide film, and a lamination film of these is formed by the CVD method or the sputtering method (FIG. 1B).

[0051] Step (B) A photoresist layer 6 is formed on the interlayer insulating film 5.

[0052] Step (C) The photoresist layer 6 is patterned by the photolithographic method (FIG. 1C). In this case, as the photo mask of the photoresist layer 6, a mask in which a pattern below the resolution limitation of the stepper is formed in the forming part of the reflection electrode is used. Thus, the photoresist layer 6 corresponding to the forming part of a contact hole H_1 formed on the source S or the drain D in the interlayer insulating film 5 and a transmission part T of a pixel can be removed completely. The photoresist layer 6 corresponding to the forming part of the reflection electrode can be also formed with surface roughness.

[0053] A more specific shape of the photo mask can be determined by experimentally obtaining the relation

between a pattern of the photo mask, the reduced amount of the film thickness of the photoresist layer and exposure time. For example, when a pattern of line/space (hereinafter, called L/S) as shown in **FIG. 5** is exposed in the stepper, the relation between the reduced amount of the film thickness of the photoresist layer and exposure time is changed in accordance with L/S, as shown in **FIG. 6**. In **FIG. 6**., the window outside the graph indicates that S is above the resolution of the exposing device. The numerical values at the right side of the symbols such as X indicate $L(\mu\text{m})/S(\mu\text{m})$. In **FIG. 6**, when an exposure for completely opening the forming part of the contact hole of the photoresist layer is 1200 sec, $L=0.25\ \mu\text{m}$ and $S=0.50\ \mu\text{m}$ are selected, the reduced amount of the film thickness of the photoresist layer can be found to be $0.6\ \mu\text{m}$.

[0054] When the reduced amount of the film thickness of the photoresist layer is thus determined experimentally, the dot pattern as shown in **FIG. 7** may be used in place of the L/S pattern of **FIG. 5**.

[0055] Another more specific shape of the photo mask can be calculated from a constant of the optic system. The effective transmissivity of the photo mask can control the film thickness of the photoresist layer.

[0056] As the actual pattern of the photo mask, a pattern unresolved by the stepper is provided stepwise or continuously. For example, as shown in a photo mask **20** of **FIG. 8**, when forming a portion **21** for completely opening the photoresist layer by exposure and a portion for forming surface roughness in the photoresist layer, individual pattern portions **22** for forming the surface roughness can be a plurality of fine ring patterns in a concentric form unresolved by the stepper cannot resolve, like a pattern **22a** shown in **FIG. 9A**. Such a photo mask is used to expose and develop the photoresist layer. A portion completely opened and a portion formed with the surface roughness can be produced in the photoresist layer. After development, it is heated and reflowed. As shown in **FIG. 9B**, the shape of the individual patterns for forming the surface roughness of the photoresist layer **6** can be smooth.

[0057] The pattern of the photo mask may be a specific pattern corresponding to the shape of surface roughness for increasing the reflectivity of the reflection electrode in the specific direction so as to be formed in the interlayer insulating film **5**. For example, as shown in **FIG. 10A**, a plurality of ring patterns are eccentric. The photo mask is used to expose and develop the photoresist layer **6**, which is then re-flowed as needed. As shown in **FIG. 10B**, in the shape of the individual patterns for forming the surface roughness of the photoresist layer **6**, the slope of one of the side surfaces can be steep, and the slope of the other side surface can be gentle.

[0058] The reflectivity of the reflection electrode depends on the level difference in the pattern formed in the photoresist layer **6**, as shown in **FIG. 11**. The level difference in the pattern depends on the pattern shape of the photo mask and an exposure. The pattern of the photo mask and an exposure of the photoresist layer **6** are set suitably so that the reflection electrode is formed into the level difference to provide a predetermined reflectivity.

[0059] Using the photoresist layer **6** thus patterned as an etching mask, the interlayer insulating film **5** is dry etched.

The shape of the photoresist layer **6** is transferred onto the interlayer insulating film **5**. The following step (D) is then performed.

[0060] Step (D) Using the photoresist layer **6** patterned in the above-mentioned step (C) as an etching mask, the interlayer insulating film **5** is etched by a dry etching method of a resist recessing method such as an RIE method or an ICP method (**FIG. 1D**). Thus, the interlayer insulating film of the forming part of the contact holes H_1 and the transmission part of the pixel is opened completely. In addition, surface roughness is formed in the interlayer insulating film of the forming part of the reflection electrode.

[0061] After the interlayer insulating film **5** is formed in the step (D), an insulating film needs not be laminated in order to form the surface roughness shape of the reflection electrode **10**, an insulating film needs not be laminated. In the following step (E), the reflection electrode **10** is formed.

[0062] Step (E) A metal having a high reflectivity such as Al, Ag, Al alloy or Ag alloy is deposited using a sputtering method to form a metal film **11**. The metal film **11** is then patterned by the photolithographic method and is etched. A source electrode S_1 and a signal wiring conductive with the source S through the contact hole H_1 , and a drain electrode D_1 and the reflection electrode **10** conductive with the drain D through the contact hole H_1 are formed at the same time (**FIG. 1E**). In this case, the metal film **11** may be of a multi-layered construction having a conductive film having a high reflectivity such as Al, Ag, Al alloy or Ag alloy and a metal film such as Cr, Mo, Ti and W.

[0063] After the reflection electrode **10** is formed, using the following steps (1) to (3), a liquid crystal display device in which an ultraviolet-reactive liquid crystal orientation film is formed on the reflection electrode **10** is produced as follows.

[0064] Step (1) A protective film **12** is formed on the reflection electrode **10** so as to eliminate the level difference in the surface roughness of the reflection electrode **10**. The protective film **12** is formed by a material transparent to a visible light for absorbing an ultraviolet light. As the specific forming material for the protective film **12**, it is possible to use, for example, an organic photoresist material such as 405G, 415G, and 420G manufactured by JSR. **FIG. 14** shows the transmission properties of the photoresist materials.

[0065] In the protective film **12**, a contact hole H_2 corresponding to the forming part of the drain electrode D_1 and an opening corresponding to the transmission part T of the pixel are patterned by the photolithographic method (**FIG. 1F**).

[0066] The thickness of the protective film **12** is preferably set so that the cell gap of the liquid crystal display cell is $\frac{1}{2}\lambda$ in the transmission part of the pixel and is $\frac{1}{4}\lambda$ in the reflection part. The cell gap of such a liquid crystal display cell is generally required to brighten the screen. In the present invention, the thickness of the protective film **12** is adjusted so as to easily form such a cell gap.

[0067] In the present invention, after the protective film **12** is formed in the step (1), a composition for an ultraviolet-reactive liquid crystal orientation film is coated onto the protective film **12** in the step (2). Preferably, before a

composition for an ultraviolet-reactive liquid crystal orientation film is coated in the step (2), as shown in FIG. 1C, a transparent conductive film 9 is formed on the protective film 12 so as to be a pattern including the transmission part T of the pixel and the reflection part R of the pixel. A transparent electrode of the transmission part T of the pixel is formed. The transparent conductive film 9 covers the reflection electrode 10. The transparent conductive film 9 is connected electrically to the reflection electrode 10 through the contact hole H₂ so as to be conductive. The pattern of the transparent conductive film 9 may be formed only in the transmission part of the pixel and the contact part of the transmission part and the reflection part of the pixel. As described above, the transparent conductive film 9 is formed to cover the reflection electrode 10, thereby electrically connecting the transparent conductive film 9 to the reflection electrode 10 so as to be conductive. The liquid crystal display cell can prevent a printing phenomenon in which Ag forming the reflection electrode 10 is transferred onto the opposing substrate.

[0068] The transparent conductive film 9 is formed so that an ITO is deposited by the sputtering method to be patterned by the photolithographic process and the etching process.

[0069] After the transparent conductive film 9 is formed, in the step (2), a coating film 31 made of a composition for an ultraviolet-reactive liquid crystal orientation film, as shown in FIG. 1H.

[0070] As the composition for an ultraviolet-reactive liquid crystal orientation film, it is possible to use a polyamic acid polymer material as a polyimide type optical orientation material disclosed in U.S. Pat. No. 5,731,405. The thickness of the coating film 31 is generally 0.02 to 0.08 μm.

[0071] Step (3) The coating film 31 formed in the step (2) is irradiated with a polarizing ultraviolet light L onto the substrate surface in the slanting direction to provide a TFT substrate formed with a liquid crystal orientation film 32 (FIG. 1I).

[0072] Irradiation of the polarizing ultraviolet light is preferably performed twice of a first irradiation for regulating the orientation direction of the liquid crystal and a second irradiation for exhibiting a pre-tilt angle.

[0073] An irradiation angle of the polarizing ultraviolet light L in the first irradiation, that is, an irradiation angle θ to the substrate surface is preferably $40^\circ \leq \theta < 90^\circ$ to prevent the contrast from being lowered. The second irradiation is preferably performed by rotating the substrate surface 45 to 90° to the first irradiation. An irradiation angle of the second irradiation is preferable so that the irradiation angle to the substrate surface is $40^\circ \leq \theta < 90^\circ$. Outside the range, the pre-tilt angle is small.

[0074] In the present invention, the coating film 31 made of a composition for an ultraviolet-reactive liquid crystal orientation film is formed on the reflection electrode 10. In spite of the fact, the coating film 31 is flattened by the protective film 12. The polarizing ultraviolet light L is irradiated at a fixed incident angle onto the coating film 31 made of a composition for an ultraviolet-reactive liquid crystal orientation film.

[0075] The polarizing ultraviolet light L passes through the coating film 31 and the protective film 12 and is then

reflected by the reflection electrode 10. The polarizing ultraviolet light is absorbed into the protective film 12. The reflection light from the reflection electrode 10 does not include the polarizing ultraviolet light. The re-irradiation phenomenon in the coating film 31 can be prevented. According to the present invention, a stable liquid crystal orientation film 32 can be obtained.

[0076] The ultraviolet-reactive liquid crystal orientation film is also formed on the opposing substrate formed with the color filter and the opposing transparent electrode. In order that the TFT substrate formed with the above-mentioned liquid crystal orientation film 32 and the opposing substrate can hold a suitable gap, a gap material is used to superpose both substrates together by a sealing material. Liquid crystals are then implanted into the resulting substrates for sealing to provide a liquid crystal display device.

[0077] In the method for producing a liquid crystal display device for performing semi-transmission liquid crystal display, there is described above the case that the reflection electrode 10 is formed by the steps (A) to (E), and the ultraviolet-reactive liquid crystal orientation film 32 is formed thereon by the steps (1) to (3). The present invention can be also applied to the case that a reflection electrode is formed by the prior art shown in FIG. 12, and the ultraviolet-reactive liquid crystal orientation film is formed thereon.

[0078] In this case, a substrate has a reflection electrode 10 formed in the reflection part R of a pixel, and a transparent electrode made of a transparent conductive film 9 formed in the transmission part T (FIG. 12I). As shown in FIG. 2A, a protective film 12 made of a material transparent to a visible light for absorbing an ultraviolet light is formed on the substrate so as to eliminate the level difference in the surface roughness of the reflection electrode 10. A coating film 31 made of a composition for an ultraviolet-reactive liquid crystal orientation film (FIG. 2B) is then formed. A polarizing ultraviolet light L is irradiated onto the coating film 31 to form a liquid crystal orientation film 32 (FIG. 2C).

[0079] The present invention can be applied not only to the semi-transmission liquid crystal display device having a reflection electrode in the reflection part R of the pixel and a transparent electrode in the transmission part T of the pixel, but also to a reflection type liquid crystal display device formed with only a reflection electrode as a pixel electrode.

[0080] In this case, the method for forming the reflection electrode 10 of the reflection type liquid crystal display device can be in accordance with the method for forming the reflection electrode 10 in the steps (A) to (E) in the method for producing a semi-transmission liquid crystal display device shown in FIGS. 1A to 1I. As shown in FIG. 3, a protective film 12 is formed on a reflection electrode 10 so as to eliminate the surface roughness of the reflection electrode 10. Then, a TFT substrate having an ultraviolet-reactive liquid crystal orientation film 32 can be produced on the protective film 12.

[0081] The method for forming the reflection electrode 10 of the reflection type liquid crystal display device may be a method in the insulating layer under the reflection electrode 10 is of a three-layer lamination construction (the interlayer insulating film 5, and the first layer 7 and the second layer

8 made of a photoresist material), as shown in FIGS. 12A to 12J. In this case, as shown in FIG. 4, a protective film 12 is formed on a reflection electrode 10 so as to produce a TFT substrate having an ultraviolet-reactive liquid crystal orientation film 32 on the protective film 12.

[0082] The present invention is described above with reference to the drawings. The present invention can employ various embodiments. The drawings each show a liquid crystal display device having a TFT of a bottom gate construction in the pixel structure. The present invention can be also applied to a liquid crystal display device having a TFT of a top gate construction in the pixel structure. The present invention can be applied not only to an active matrix type liquid crystal display device but also to a passive type liquid crystal display device.

What is claimed is:

1. A method for producing a liquid crystal display device having a reflection electrode of a reflection diffuser panel shape formed with surface roughness provided on a driving substrate and an ultraviolet-reactive liquid crystal orientation film formed on the reflection electrode, comprising the following steps (1) to (3) of:

- (1) forming a protective film made of a material transparent to a visible light for absorbing an ultraviolet light on the reflection electrode on the driving substrate side so as to eliminate the level difference in the surface roughness of the reflection electrode;
- (2) coating a composition for an ultraviolet-reactive liquid crystal orientation film onto the protective film; and
- (3) forming a liquid crystal orientation film on the coating film of the composition for a liquid crystal orientation film by irradiating a polarizing ultraviolet light onto the substrate surface in the slanting direction.

2. The producing method according to claim 1, wherein in the step (3), an irradiation angle θ of the ultraviolet light is $40^\circ \leq \theta < 90^\circ$ to the substrate surface.

3. The producing method according to claim 1 or 2, wherein after forming the protective film in the step (1) and before coating the composition for a liquid crystal orienta-

tion film in the step (2), a transparent conductive film is formed on the protective film so as to cover the reflection electrode and to be electrically conductive with the reflection electrode, and the composition for a liquid crystal orientation film in the step (2) is coated onto the transparent conductive film.

4. The producing method according to claim 1, wherein a reflection electrode is formed on a driving substrate as a pixel electrode in a reflection part of a pixel, and a transparent electrode made of a transparent conductive film is formed as a pixel electrode in a transmission part of the pixel, thereby producing a liquid crystal display device for performing semi-transmission liquid crystal display.

5. The producing method according to claim 1, wherein only a reflection electrode is formed on a driving substrate as a pixel electrode, thereby producing a liquid crystal display device for performing reflection type liquid crystal display.

6. A liquid crystal display device having a reflection electrode of a reflection diffuser panel shape formed with surface roughness provided on a driving substrate and an ultraviolet-reactive liquid crystal orientation film formed on the reflection electrode, wherein a protective film made of a material transparent to a visible light for absorbing an ultraviolet light is formed so as to eliminate the level difference in the surface roughness of the reflection electrode, and an ultraviolet-reactive liquid crystal orientation film is formed on the protective film.

7. The liquid crystal display device according to claim 6, wherein a reflection electrode is formed on a driving substrate as a pixel electrode in a reflection part of a pixel, and a transparent electrode made of a transparent conductive film is formed as a pixel electrode in a transmission part of the pixel, thereby performing semi-transmission liquid crystal display.

8. The liquid crystal display device according to claim 6, wherein only a reflection electrode is formed on a driving substrate as a pixel electrode, thereby performing reflection type liquid crystal display.

* * * * *

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|----------------|---------------------------------------------------------------|---------|------------|
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摘要(译)

在具有形成有表面粗糙度的反射漫射板形状的反射电极的液晶显示装置中，通过光学取向技术在反射电极上形成用于实现预定的预倾角的液晶取向膜。一种液晶显示装置，其具有形成有设置在驱动基板上的表面粗糙度的反射漫射板形状的反射电极和形成在反射电极上的紫外线反应性液晶取向膜，通过步骤（1）制造，用于形成保护由对可见光透明的材料制成的薄膜，用于在驱动基板侧的反射电极上吸收紫外光，从而消除反射电极的表面粗糙度的高度差；步骤（2）：将用于紫外线反应性液晶取向膜的组合物涂布在保护膜上；步骤（3）：通过在倾斜方向上将偏振紫外光L照射到基板表面上，在液晶取向膜用组合物的涂膜上形成液晶取向膜。

